NSN 5961-01-464-0830

Diode Semiconductor Device - Page 1 of 1

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Inclosure Material:

Glass

Overall Length:

7.490 millimeters

Terminal Length:

5.970 millimeters

Overall Width:

2.190 millimeters

End Application:

6625-01-443-0552

Mounting Facility Quantity:

3

Mounting Method:

Terminal

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

60.0 breakdown voltage, collector to emitter, sustained and 60.0 breakdown voltage, collector-to-base, emitter open

Current Rating Per Characteristic:

5.00 milliamperes source cutoff current

Power Rating Per Characteristic:

10.0 watts small-signal output power, common-base preset

Maximum Operating Tempurature Per Measurement Point:

-55.0 degrees celsius case and 150.0 degrees celsius case

Special Features:

Low-frequency power silicon pnp bjt

Terminal Type And Quantity:

3 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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